

# NPN SILICON RF TRANSISTOR 2SC4227

### NPN EPITAXIAL SILICON RF TRANSISTOR FOR HIGH-FREQUENCY LOW-NOISE AMPLIFICATION 3-PIN SUPER MINIMOLD

### **DESCRIPTION**

The 2SC4227 is a low supply voltage transistor designed for VHF, UHF low noise amplifier.

It is suitable for a high density surface mount assembly since the transistor has been applied 3-pin super minimold package.

#### **FEATURES**

- Low noise : NF = 1.4 dB TYP. @ VcE = 3 V, Ic = 7 mA, f = 1 GHz
- High gain :  $|S_{21e}|^2 = 12 \text{ dB TYP.}$  @ VcE = 3 V, Ic = 7 mA, f = 1 GHz
- · 3-pin super minimold package

#### ★ ORDERING INFORMATION

Part Number	Quantity	Supplying Form
2SC4227	50 pcs (Non reel)	8 mm wide embossed taping
2SC4227-T1	3 kpcs/reel	Pin 3 (Collector) face the perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office.

The unit sample quantity is 50 pcs.

#### ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	Vcво	20	V
Collector to Emitter Voltage	Vceo	10	V
Emitter to Base Voltage	V <sub>EBO</sub>	1.5	V
Collector Current	lc	65	mA
Total Power Dissipation	Ptot Note	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature	T <sub>stg</sub>	-65 to +150	°C

Note Free air

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

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The mark ★ shows major revised points.

Printed in Japan



### **ELECTRICAL CHARACTERISTICS (TA = +25°C)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit	
DC Characteristics							
Collector Cut-off Current	Ісво	VcB = 10 V, IE = 0 mA	-	-	0.8	μΑ	
Emitter Cut-off Current	ІЕВО	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0 mA	-	-	0.8	μΑ	
DC Current Gain	hfe Note 1	VcE = 3 V, Ic = 7 mA	40	-	240	-	
RF Characteristics							
Gain Bandwidth Product	fτ	VcE = 3 V, Ic = 7 mA	4.5	7.0	-	GHz	
Insertion Power Gain	S <sub>21e</sub>   <sup>2</sup>	VcE = 3 V, Ic = 7 mA, f = 1 GHz	10	12	-	dB	
Noise Figure	NF	VcE = 3 V, Ic = 7 mA, f = 1 GHz	-	1.4	2.7	dB	
Reverse Transfer Capacitance	Cre Note 2	VcB = 3 V, IE = 0 mA, f = 1 MHz	-	0.45	0.9	pF	

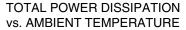
**Notes 1.** Pulse measurement: PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2%

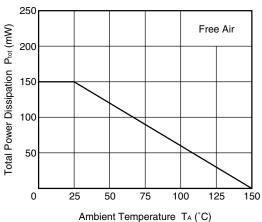
2. Collector to base capacitance when the emitter grounded

### **hfe CLASSIFICATION**

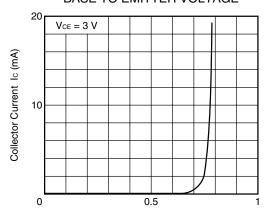
Rank	R33	R34	R35
Marking	R33	R34	R35
h <sub>FE</sub> Value	40 to 90	70 to 150	110 to 240

### TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)



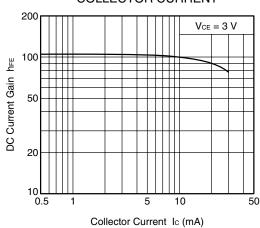


# COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



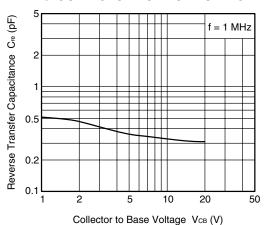
Base to Emitter Voltage  $\ensuremath{V_{BE}}$  (V)

# DC CURRENT GAIN vs. COLLECTOR CURRENT

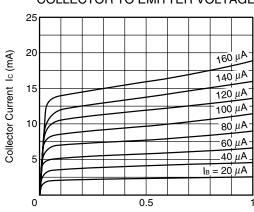


Remark The graphs indicate nominal characteristics.

### REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE

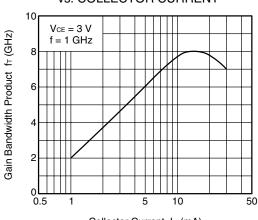


COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE



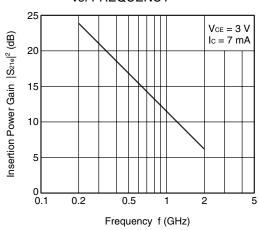
Collector to Emitter Voltage VcE (V)

# GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

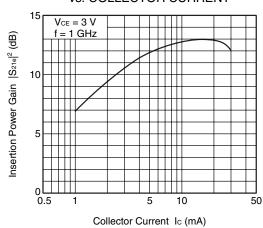


Collector Current Ic (mA)

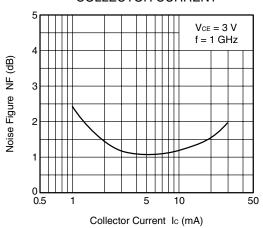
# INSERTION POWER GAIN vs. FREQUENCY



# INSERTION POWER GAIN vs. COLLECTOR CURRENT



# NOISE FIGURE vs. COLLECTOR CURRENT



Remark The graphs indicate nominal characteristics.

### **S-PARAMETERS**

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

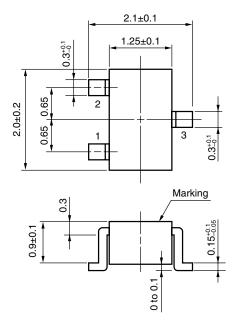
Click here to download S-parameters.

 $[\mathsf{RF} \ \mathsf{and} \ \mathsf{Microwave}] \to [\mathsf{Device} \ \mathsf{Parameters}]$ 

URL http://www.ncsd.necel.com/

### **PACKAGE DIMENSIONS**

### 3-PIN SUPER MINIMOLD (UNIT: mm)



### **PIN CONNECTIONS**

- 1. Emitter
- 2. Base
- 3. Collector

(EIAJ : SC-70)

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